FAIRCHILD SEMICONDUCTOR™

March 2002
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74LVT32245 • 74LVTH32245
Low Voltage 32-Bit Transceiver with 3-STATE Outputs

General Description

The LVT32245 and LVTH32245 contain thirty-two non-inverting bidirectional buffers with 3-STATE outputs and are intended for bus oriented applications. The devices are byte controlled. Each byte has separate control inputs which can be shorted together for full 32-bit operation. The $T/\overline{R}$ inputs determine the direction of data flow through the device. The $\overline{OE}$ inputs disable both the A and B ports by placing them in a high impedance state.

The LVTH32245 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

These non-inverting transceivers are designed for low voltage (3.3V) V_{CC} applications, but with the capability to provide a TTL interface to a 5V environment. The LVT32245 and LVTH32245 are fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining low power dissipation.

Features

- Input and output interface capability to systems at 5V V_{CC}
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs (74LVTH32245), also available without bushold feature (74LVT32245).
- Live insertion/extraction permitted
- Power Up/Down high impedance provides glitch-free bus loading
- Outputs source/sink −32 mA/+64 mA
- ESD performance:
  Human-body model > 2000V
  Machine model > 200V
  Charged-device model > 1000V
- Packaged in plastic Fine-Pitch Ball Grid Array (FBGA)

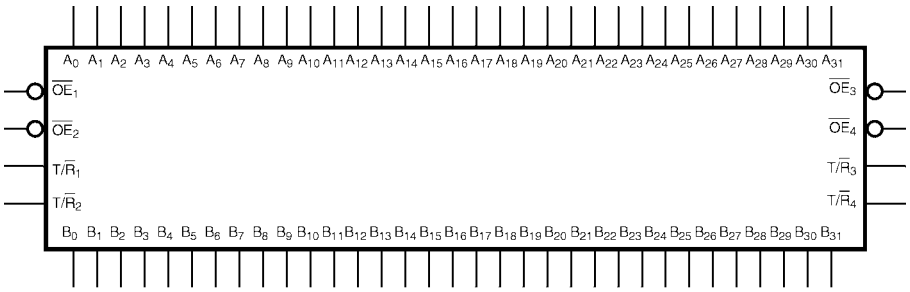
Ordering Code:

Order Number	Package Number	Package Description
74LVT32245G (Note 1)(Note 2)	BGA96A (Preliminary)	96-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide
74LVTH32245G (Note 1)(Note 2)	BGA96A	96-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide

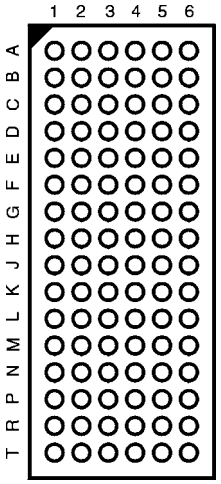
Note 1: Ordering code "G" indicates Trays.

Note 2: Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

Logic Symbol



Connection Diagram



(Top Thru View)

Pin Descriptions

Pin Names	Description
$\overline{OE}_n$	Output Enable Input (Active LOW)
$T/\overline{R}_n$	Transmit/Receive Input
A_0–A_{31}	Side A Inputs/3-STATE Outputs
B_0–B_{31}	Side B Inputs/3-STATE Outputs

FBGA Pin Assignments

	1	2	3	4	5	6
A	B_1	B_0	$T/\overline{R}_1$	$\overline{OE}_1$	A_0	A_1
B	B_3	B_2	GND	GND	A_2	A_3
C	B_5	B_4	V_{CC1}	V_{CC1}	A_4	A_5
D	B_7	B_6	GND	GND	A_6	A_7
E	B_9	B_8	GND	GND	A_8	A_9
F	B_{11}	B_{10}	V_{CC1}	V_{CC1}	A_{10}	A_{11}
G	B_{13}	B_{12}	GND	GND	A_{12}	A_{13}
H	B_{14}	B_{15}	$T/\overline{R}_2$	$\overline{OE}_2$	A_{15}	A_{14}
J	B_{17}	B_{16}	$T/\overline{R}_3$	$\overline{OE}_3$	A_{16}	A_{17}
K	B_{19}	B_{18}	GND	GND	A_{18}	A_{19}
L	B_{21}	B_{20}	V_{CC2}	V_{CC2}	A_{20}	A_{21}
M	B_{23}	B_{22}	GND	GND	A_{22}	A_{23}
N	B_{25}	B_{24}	GND	GND	A_{24}	A_{25}
P	B_{27}	B_{26}	V_{CC2}	V_{CC2}	A_{26}	A_{27}
R	B_{29}	B_{28}	GND	GND	A_{28}	A_{29}
T	B_{30}	B_{31}	$T/\overline{R}_4$	$\overline{OE}_4$	A_{31}	A_{30}

Truth Tables

Inputs		Outputs
$\overline{OE}_1$	$T/\overline{R}_1$	
L	L	Bus B_0–B_7 Data to Bus A_0–A_7
L	H	Bus A_0–A_7 Data to Bus B_0–B_7
H	X	HIGH–Z State on A_0–A_7,B_0–B_7

Inputs		Outputs
$\overline{OE}_3$	$T/\overline{R}_3$	
L	L	Bus B_{16}–B_{23} Data to Bus A_{16}–A_{23}
L	H	Bus A_{16}–A_{23} Data to Bus B_{16}–B_{23}
H	X	HIGH–Z State on A_{16}–A_{23},B_{16}–B_{23}

Inputs		Outputs
$\overline{OE}_2$	$T/\overline{R}_2$	
L	L	Bus B_8–B_{15} Data to Bus A_8–A_{15}
L	H	Bus A_8–A_{15} Data to Bus B_8–B_{15}
H	X	HIGH–Z State on A_8–A_{15},B_8–B_{15}

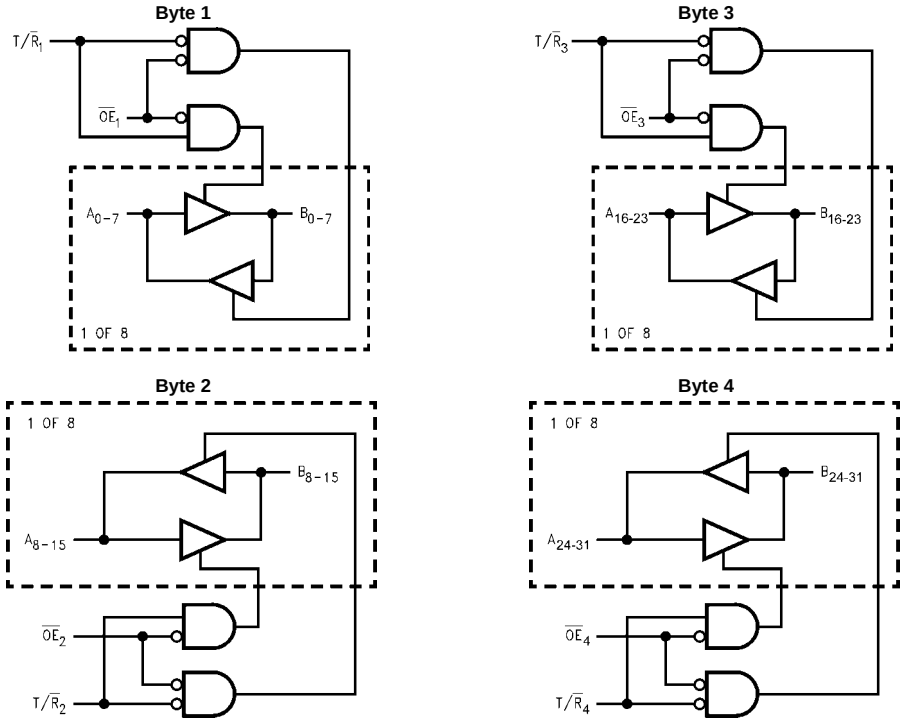
Inputs		Outputs
$\overline{OE}_4$	$T/\overline{R}_4$	
L	L	Bus B_{24}–B_{31} Data to Bus A_{24}–A_{31}
L	H	Bus B_{24}–A_{31} Data to Bus B_{24}–B_{31}
H	X	HIGH–Z State on A_{24}–A_{31},B_{24}–B_{31}

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial
Z = High Impedance

Functional Description

The LVT32245 and LVTH32245 contain thirty-two non-inverting bidirectional buffers with 3-STATE outputs. The device is byte controlled with each byte functioning identically, but independent of the other. The control pins can be shorted together to obtain 16-bit or full 32-bit operation.

Logic Diagrams



V_{CC1} is associated with Bytes 1 and 2.

V_{CC2} is associated with Bytes 3 and 4.

Note: Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings(Note 3)

Symbol	Parameter	Value	Conditions	Units
V_{CC}	Supply Voltage	−0.5 to +4.6		V
V_I	DC Input Voltage	−0.5 to +7.0		V
V_O	Output Voltage	−0.5 to +7.0	Output in 3-STATE	V
		−0.5 to +7.0	Output in HIGH or LOW State (Note 4)	
I_{IK}	DC Input Diode Current	−50	V_I < GND	mA
I_{OK}	DC Output Diode Current	−50	V_O < GND	mA
I_O	DC Output Current	64	Output at HIGH State, $V_O > V_{CC}$	mA
		128	Output at LOW State, $V_O > V_{CC}$	
I_{CC}	DC Supply Current per Supply Pin	±64		mA
I_{GND}	DC Ground Current per Ground Pin	±128		mA
T_{STG}	Storage Temperature Range	−65 to +150		°C

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
V_{CC}	Supply Voltage	2.7	3.6	V
V_I	Input Voltage	0	5.5	V
I_{OH}	HIGH-Level Output Current		−32	mA
I_{OL}	LOW-Level Output Current		64	mA
T_A	Free-Air Operating Temperature	−40	+85	°C
$\Delta t/\Delta V$	Input Edge Rate, V_{IN} = 0.8V–2.0V, V_{CC} = 3.0V	0	10	ns/V

Note 3: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied.

Note 4: I_O Absolute Maximum Ratings must be observed.

DC Electrical Characteristics

Symbol	Parameter		V_{CC} (V)	T_A = −40°C to +85°C Min	T_A = −40°C to +85°C Max	Units	Conditions
V_{IK}	Input Clamp Diode Voltage		2.7		−1.2	V	I_I = −18 mA
V_{IH}	Input HIGH Voltage		2.7–3.6	2.0		V	$V_O \le 0.1V$ or
V_{IL}	Input LOW Voltage		2.7–3.6		0.8	V	$V_O \ge V_{CC} - 0.1V$
V_{OH}	Output HIGH Voltage		2.7–3.6	V_{CC} − 0.2		V	I_{OH} = −100 µA
			2.7	2.4			I_{OH} = −8 mA
			3.0	2.0			I_{OH} = −32 mA
V_{OL}	Output LOW Voltage		2.7		0.2	V	I_{OL} = 100 µA
			2.7		0.5		I_{OL} = 24 mA
			3.0		0.4		I_{OL} = 16 mA
			3.0		0.5		I_{OL} = 32 mA
			3.0		0.55		I_{OL} = 64 mA
$I_{I(HOLD)}$ (Note 5)	Bushold Input Minimum Drive		3.0	75		µA	V_I = 0.8V
				−75			V_I = 2.0V
$I_{I(OD)}$ (Note 5)	Bushold Input Over-Drive Current to Change State		3.0	500		µA	(Note 6)
				−500			(Note 7)
I_I	Input Current		3.6		10	µA	V_I = 5.5V
		Control Pins	3.6		±1		V_I = 0V or V_{CC}
		Data Pins	3.6		−5		V_I = 0V
					1		$V_I = V_{CC}$
I_{OFF}	Power Off Leakage Current		0		±100	µA	0V ≤ V_I or V_O ≤ 5.5V
$I_{PU/PD}$	Power Up/Down 3-STATE Output Current		0–1.5		±100	µA	V_O = 0.5V to 3.0V, V_I = GND or V_{CC}
I_{OZL}	3-STATE Output Leakage Current		3.6		−5	µA	V_O = 0.5V
I_{OZL} (Note 5)	3-STATE Output Leakage Current		3.6		−5	µA	V_O = 0.0V
I_{OZH}	3-STATE Output Leakage Current		3.6		5	µA	V_O = 3.0V

DC Electrical Characteristics (Continued)

Symbol	Parameter	V_{CC} (V)	$T_A = -40°C$ to $+85°C$		Units	Conditions
			Min	Max		
I_{OZH} (Note 5)	3-STATE Output Leakage Current	3.6		5	μA	$V_O = 3.6V$
$I_{OZH}+$	3-STATE Output Leakage Current	3.6		10	μA	$V_{CC} < V_O \leq 5.5V$
I_{CCH}	Power Supply Current V_{CC1} or V_{CC2}	3.6		0.19	mA	Outputs HIGH
I_{CCL}	Power Supply Current V_{CC1} or V_{CC2}	3.6		5.0	mA	Outputs LOW
I_{CCZ}	Power Supply Current V_{CC1} or V_{CC2}	3.6		0.19	mA	Outputs Disabled
$I_{CCZ}+$	Power Supply Current V_{CC1} or V_{CC2}	3.6		0.19	mA	$V_{CC} \leq V_O \leq 5.5V$, Outputs Disabled
ΔI_{CC}	Increase in Power Supply Current (Note 8) V_{CC1} or V_{CC2}	3.6		0.2	mA	One Input at $V_{CC} - 0.6V$ Other Inputs at V_{CC} or GND

Note 5: Applies to bushold versions only (74LVTH32245).

Note 6: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 7: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

Note 8: This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.

Dynamic Switching Characteristics (Note 9)

Symbol	Parameter	V_{CC} (V)	$T_A = 25°C$			Units	Conditions $C_L = 50$ pF, $R_L = 500\Omega$
			Min	Typ	Max		
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	3.3		0.8		V	(Note 10)
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	3.3		−0.8		V	(Note 10)

Note 9: Characterized in SSOP package. Guaranteed parameter, but not tested.

Note 10: Max number of outputs defined as (n). n–1 data inputs are driven 0V to 3V. Output under test held LOW.

AC Electrical Characteristics

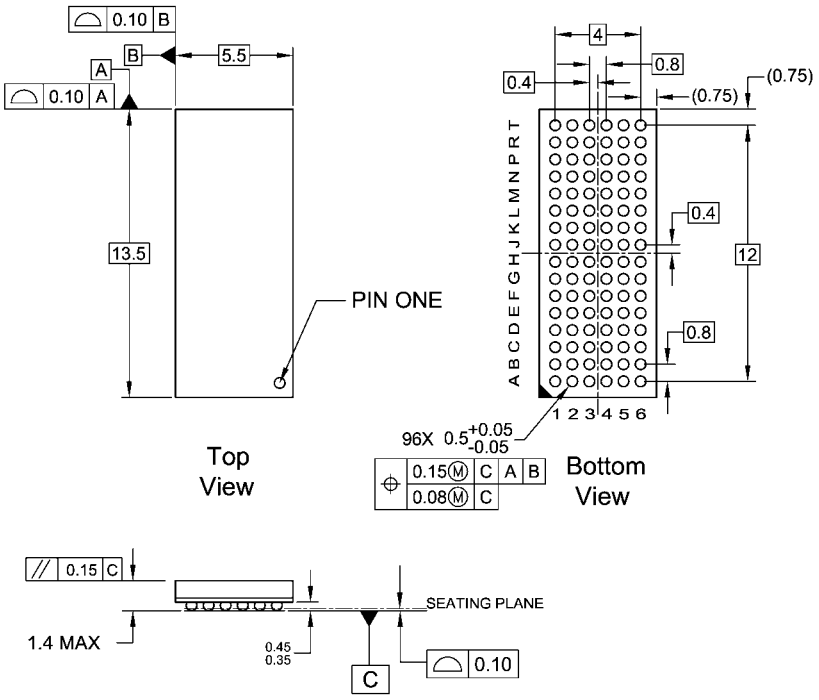
Symbol	Parameter	$T_A = -40°C$ to $+85°C$, $C_L = 50$ pF, $R_L = 500\Omega$				Units
		$V_{CC} = 3.3V \pm 0.3V$		$V_{CC} = 2.7V$		
		Min	Max	Min	Max	
t_{PLH}	Propagation Delay Data to Output	1.5	3.5	1.5	3.9	ns
t_{PHL}		1.3	3.5	1.3	3.9	
t_{PZH}	Output Enable Time	1.5	4.5	1.5	5.3	ns
t_{PZL}		1.6	5.3	1.6	6.9	
t_{PHZ}	Output Disable Time	2.3	5.4	2.3	6.1	ns
t_{PLZ}		2.2	5.1	2.2	5.4	

Capacitance (Note 11)

Symbol	Parameter	Conditions	Typical	Units
C_{IN}	Input Capacitance	$V_{CC} = 0V$, $V_I = 0V$ or V_{CC}	4	pF
$C_{I/O}$	Input/Output Capacitance	$V_{CC} = 3.0V$, $V_O = 0V$ or V_{CC}	8	pF

Note 11: Capacitance is measured at frequency f = 1 MHz, per MIL-STD-883, Method 3012.

Physical Dimensions inches (millimeters) unless otherwise noted



NOTES:

A. THIS PACKAGE CONFORMS TO JEDEC M0-205
B. ALL DIMENSIONS IN MILLIMETERS
C. LAND PATTERN RECOMMENDATION: NSMD (Non Solder Mask Defined)
.35MM DIA PADS WITH A SOLDERMASK OPENING OF .45MM CONCENTRIC TO PADS
D. DRAWING CONFORMS TO ASME Y14.5M-1994

BGA96ArevE

96-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide
Package Number BGA96A